

CLAIM AMENDMENTS

1. (Canceled)

2. (Currently amended) A semiconductor light receiving element comprising (a) a light receiving layer comprising a GaN group semiconductor, wherein the light receiving layer is a first conductivity type layer, (b) and an electrode formed on one surface of the light receiving layer as a light receiving surface in such a manner that the light can enter the light receiving layer, and (c) wherein the light receiving element is a Schottky barrier type light receiving element in which light enters a depletion layer formed under the electrode, which depletion layer extends to cover a small area around the electrode from the side the electrode is formed, said light receiving layer is a first conductivity type layer, said wherein (i) the light receiving element is a Schottky barrier type light receiving element in which light enters the depletion layer, (ii) the electrode formed on said the light receiving surface comprises at least a Schottky electrode, and (iii) a total of boundary lines between areas of the light receiving surface covered with the Schottky electrode and exposed areas is longer than the length of the outer periphery of the light receiving surface.

3. (Original) The light receiving element of claim 2, wherein the Schottky electrode has a wiring pattern formed by strip conductors in combination.

4. (Original) The light receiving element of claim 2, wherein the strip conductors have a width of 0.1  $\mu\text{m}$  – 2000  $\mu\text{m}$ .

5. (Original) The light receiving element of claim 2, wherein the wiring pattern is a comblike pattern.

6. (Previously amended) The light receiving element of claim 2, wherein the light receiving layer is an uppermost layer of a laminate comprising one or more layers comprising a first conductivity type GaN group semiconductor formed on a crystal substrate, wherein the light receiving element comprises an ohmic electrode formed on a layer other than the light receiving layer.

7. (Original) The light receiving element of claim 6, wherein the crystal substrate is made from a conductive material and the ohmic electrode is formed on the crystal substrate.

In re Appln. of Tadatomo et al.  
Application No. 09/787,502

[ 8.-12. (Canceled) ]

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